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DFT study of F atom adsorption on Si(001) surface

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Abstract : We have investigated the initial adsorption of a fluorine (F) atom on Si(001) surface by means of first-principles calculations using pseudopotential method implemented in SIESTA code. Three high-symmetric adsorption sites of F on Si(100) were examined : top, bridge and hollow sites. For an F atom adsorbed on perfect Si(001) surface, we found that F atom prefer the bridge adsorption site with a high adsorption energy of 6.47eV. However, in the relaxed case, the adsorption of an F atom leads to a Si(001)-2×1 surface reconstruction and the most stable adsorption site corresponds to the dangling bond site of a Si(100) surface top layer. The Si-F bond is calculated to be 1.67 Å and the adsorption energy of the F atom is evaluated to be 6.51eV.

Keywords : DFT, SIESTA, Silicon, fluorine, adsorption